Complementary Silicon High-Power Transistors

These PowerBase complementary transistors are designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc-to-dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055.

Features

- High Current-Gain Bandwidth
- Safe Operating Area
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage 2N3055AG MJ15015G, MJ15016G	V _{CEO}	60 120	Vdc
Collector–Base Voltage 2N3055AG MJ15015G, MJ15016G	V _{CBO}	100 200	Vdc
Collector–Emitter Voltage Base Reversed Biased 2N3055AG MJ15015G, MJ15016G	V _{CEV}	100 200	Vdc
Emitter-Base Voltage	V _{EBO}	7.0	Vdc
Collector Current – Continuous	I _C	15	Adc
Base Current	Ι _Β	7.0	Adc
Total Device Dissipation © T _C = 25°C 2N3055AG MJ15015G, MJ15016G Derate above 25°C 2N3055AG MJ15015G, MJ15016G	P _D	115 180 0.65 1.03	W W W/°C W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC Registered Data. (2N3055A)

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	1.52	0.98	°C/W

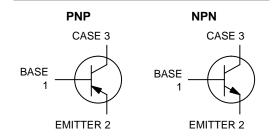
^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

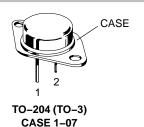


ON Semiconductor®

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15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60, 120 VOLTS – 115, 180 WATTS





MARKING DIAGRAMS

STYLE 1





2N3055A = Device Code MJ1501x = Device Code

x = 5 or 6

G = Pb-Free Package A = Assembly Location

Y = Year WW = Work Week MEX = Country of Origin

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS (Note 2)		•			•
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 200 mAdc, I _B = 0)	2N3055AG MJ15015G, MJ15016G	V _{CEO(sus)}	60 120	_ _	Vdc
Collector Cutoff Current $ (V_{CE} = 30 \text{ Vdc}, V_{BE(off)} = 0 \text{ Vdc}) $ $ (V_{CE} = 60 \text{ Vdc}, V_{BE(off)} = 0 \text{ Vdc}) $	2N3055AG MJ15015G, MJ15016G	I _{CEO}	- -	0.7 0.1	mAdc
Collector Cutoff Current (Note 3) (V _{CEV} = Rated Value, V _{BE(off)} = 1.5 Vdc)	2N3055AG MJ15015G, MJ15016G	I _{CEV}	- -	5.0 1.0	mAdc
Collector Cutoff Current (V_{CEV} = Rated Value, $V_{BE(off)}$ = 1.5 Vdc, T_C = 150°C)	2N3055AG MJ15015G, MJ15016G	I _{CEV}	_ _ _	30 6.0	mAdc
Emitter Cutoff Current (V _{EB} = 7.0 Vdc, I _C = 0)	2N3055AG MJ15015G, MJ15016G	I _{EBO}	- -	5.0 0.2	mAdc
SECOND BREAKDOWN (Note 3)					•
Second Breakdown Collector Current with Base (t = 0.5 s non-repetitive) (V _{CE} = 60 Vdc)	Forward Biased 2N3055AG MJ15015G, MJ15016G	I _{S/b}	1.95 3.0	_ _	Adc
ON CHARACTERISTICS (Note 2 and 3)		l.			
DC Current Gain $(I_C = 4.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc})$ $(I_C = 4.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$ $(I_C = 10 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$		h _{FE}	10 20 5.0	70 70 –	_
Collector–Emitter Saturation Voltage ($I_C = 4.0$ Adc, $I_B = 400$ mAdc) ($I_C = 10$ Adc, $I_B = 3.3$ Adc) ($I_C = 15$ Adc, $I_B = 7.0$ Adc)		V _{CE(sat)}	- - -	1.1 3.0 5.0	Vdc
Base–Emitter On Voltage (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc)		V _{BE(on)}	0.7	1.8	Vdc
DYNAMIC CHARACTERISTICS (Note 3)					
Current–Gain – Bandwidth Product (I _C = 1.0 Adc, V _{CE} = 4.0 Vdc, f = 1.0 MHz)	2N3055AG, MJ15015G MJ15016G	f _T	0.8 2.2	6.0 18	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{ob}	60	600	pF
SWITCHING CHARACTERISTICS (2N3055AG	only) (Note 3)				
RESISTIVE LOAD					
Delay Time		t _d	_	0.5	μS
Rise Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 4.0 \text{ Adc},$	t _r	-	4.0	μs
Storage Time	$I_{B1} = I_{B2} = 0.4 \text{ Adc},$ $t_p = 25 \mu\text{s} \text{ Duty Cycle} \leq 2\%$	t _s	-	3.0	μs
Fall Time		t _f	_	6.0	μs

Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.
 Indicates JEDEC Registered Data. (2N3055A)

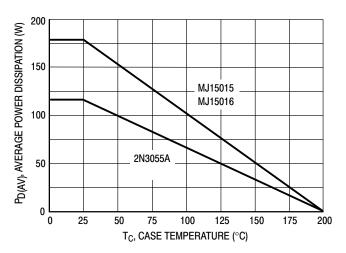


Figure 1. Power Derating

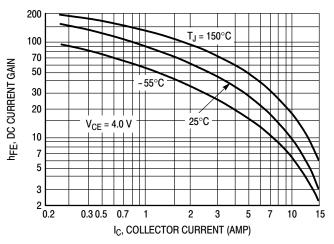


Figure 2. DC Current Gain

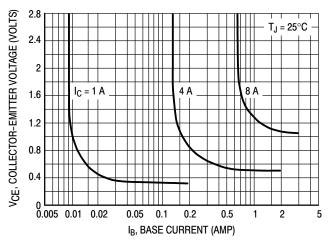


Figure 3. Collector Saturation Region

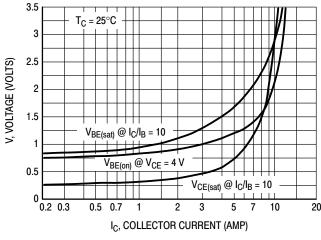


Figure 4. "On" Voltages

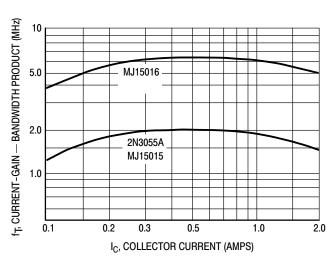
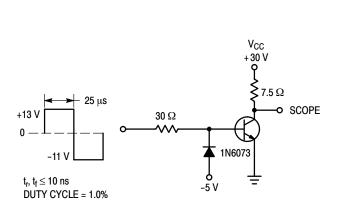


Figure 5. Current-Gain - Bandwidth Product



10 7 V_{CC} = 30 V 5 I_C/I_B = 10 T_J = 25°C 0.5 0.3 0.2 0.1 0.2 0.3 0.5 0.7 1 2 3 5 7 10 15 I_C, COLLECTOR CURRENT (AMP)

Figure 6. Switching Times Test Circuit (Circuit shown is for NPN)

Figure 7. Turn-On Time

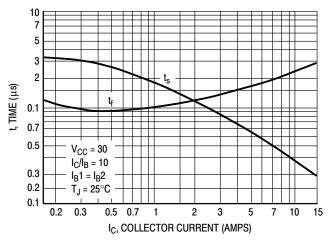


Figure 8. Turn-Off Times

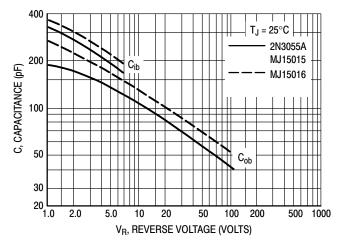


Figure 9. Capacitances

COLLECTOR CUT-OFF REGION

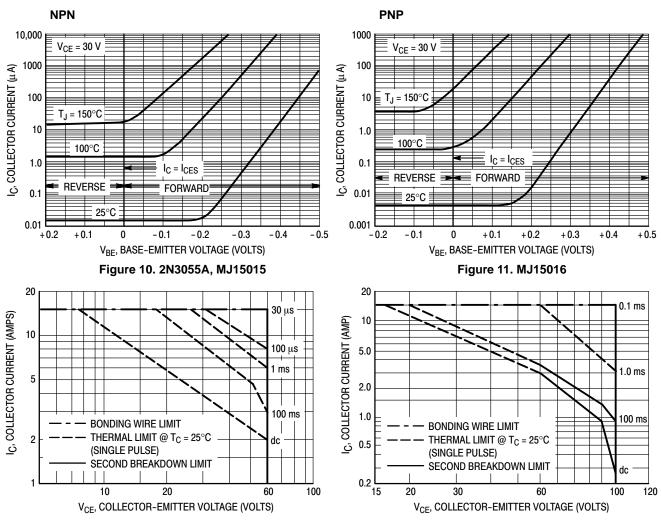


Figure 12. Forward Bias Safe Operating Area 2N3055A

There are two limitations on the power handling ability of a transistor: average junction temperature and second

limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

breakdown. Safe Operating area curves indicate I_C - V_{CE}

Figure 13. Forward Bias Safe Operating Area MJ15015, MJ15016

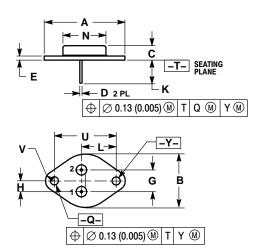
The data of Figures 12 and 13 is based on $T_C = 25\,^{\circ}\mathrm{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

ORDERING INFORMATION

Device	Package	Shipping
2N3055AG	TO-204 (Pb-Free)	100 Units / Tray
MJ15015G	TO-204 (Pb-Free)	100 Units / Tray
MJ15016G	TO-204 (Pb-Free)	100 Units / Tray

PACKAGE DIMENSIONS

TO-204 (TO-3)CASE 1-07
ISSUE Z



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	1.550 REF		39.37 REF	
В		1.050		26.67
С	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
Н	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N		0.830		21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
٧	0.131	0.188	3.33	4.77

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

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